# 1. General description

PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN complement: PBSS4130QA.

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

## 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-1	Α
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; pulsed	-	-	-1.5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	160	240	mΩ



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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	E	emitter		В
3	С	collector	4 3	'*_
4	С	collector	2	sym132
			Transparent top view DFN1010D-3 (SOT1215)	

## 6. Ordering information

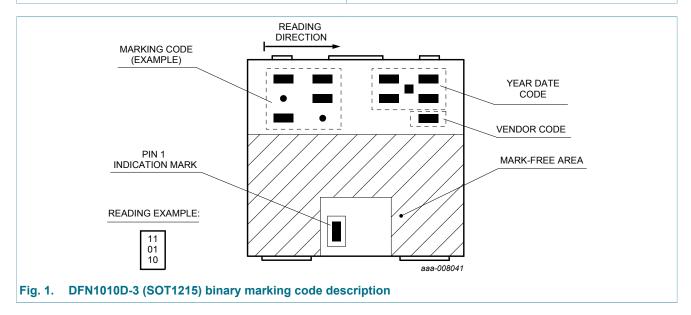
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5130QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5130QA	00 10 10



PBSS5130QA

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## 8. Limiting values

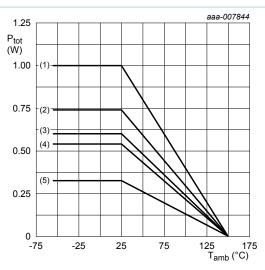
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
$V_{CEO}$	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V
I <sub>C</sub>	collector current			-	-1	Α
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; pulsed		-	-1.5	Α
I <sub>B</sub>	base current			-	-0.3	Α
I <sub>BM</sub>	peak base current	t <sub>p</sub> ≤ 1 ms; pulsed		-	-1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

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- (1) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (2) FR4 PCB, single-sided copper, 6 cm<sup>2</sup>
- (3) FR4 PCB, single-sided copper, 1 cm<sup>2</sup>
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

Fig. 2. Power derating curves

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	385	K/W
	from junction to ambient		[2]	-	-	209	K/W
ambient	ambient		[3]	-	-	169	K/W
			[4]	-	-	232	K/W
			<u>[5]</u>	-	-	125	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

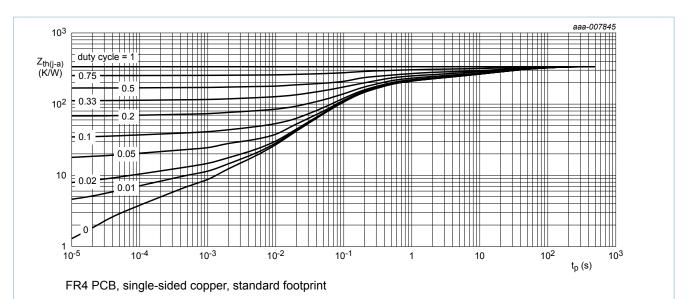


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

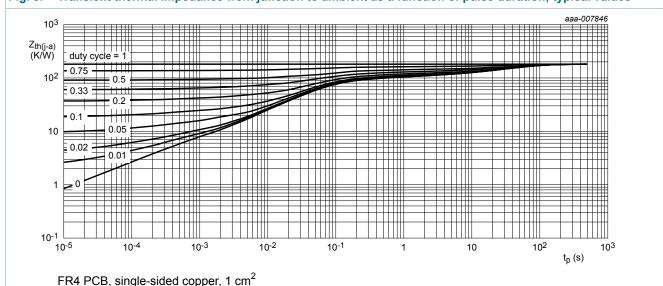


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

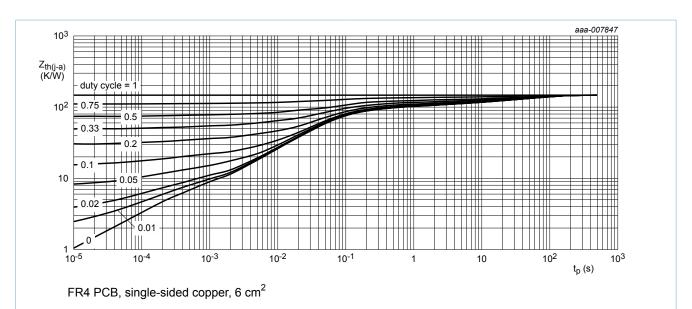


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

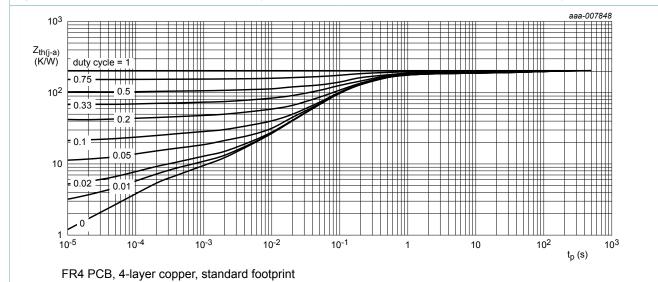
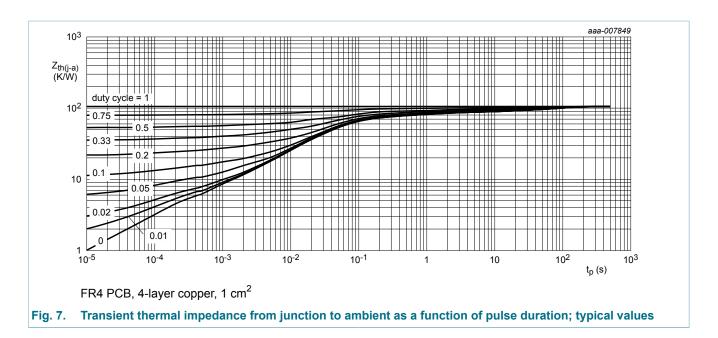


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 30 V, 1 A PNP low VCEsat (BISS) transistor



### 10. Characteristics

Table 7. Characteristics

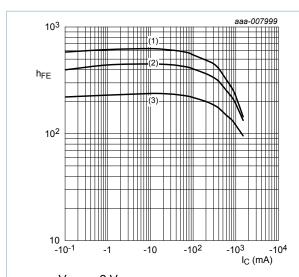
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -24 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	$V_{CB}$ = -24 V; $I_{E}$ = 0 A; $T_{j}$ = 150 °C	-	-	-50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -24 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C; pulsed	250	425	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C; pulsed	180	295	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed	130	200	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-85	-130	mV
		$I_C$ = -1 A; $I_B$ = -50 mA; $t_p \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-180	-260	mV
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-160	-240	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	160	240	mΩ

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### 30 V, 1 A PNP low VCEsat (BISS) transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>BEsat</sub> base-em voltage	base-emitter saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-0.88	-1	V
		$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	-0.93	-1.05	V
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	-	-0.96	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	-	-0.78	-0.9	V
t <sub>d</sub>	delay time	$V_{CC}$ = -10 V; $I_{C}$ = -0.5 A; $I_{Bon}$ = -25 mA;	-	10	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 25 mA; T <sub>amb</sub> = 25 °C	-	30	-	ns
t <sub>on</sub>	turn-on time		-	40	-	ns
t <sub>s</sub>	storage time		-	270	-	ns
t <sub>f</sub>	fall time		-	45	-	ns
t <sub>off</sub>	turn-off time		-	315	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	120	170	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	14	16	pF



 $V_{CE} = -2 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 8. DC current gain as a function of collector current; typical values

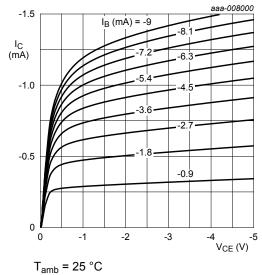
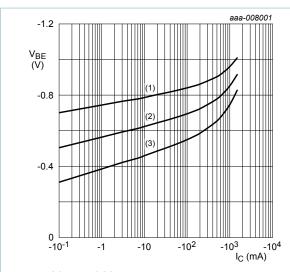


Fig. 9. Collector current as a function of collector-

emitter voltage; typical values



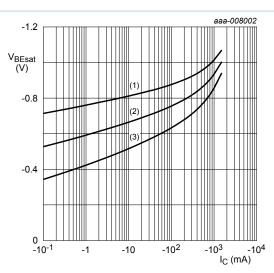
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 10. Base-emitter voltage as a function of collector current; typical values



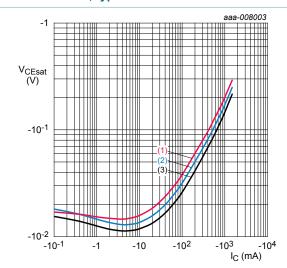
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values



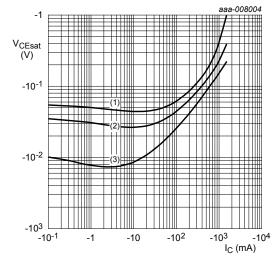


(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

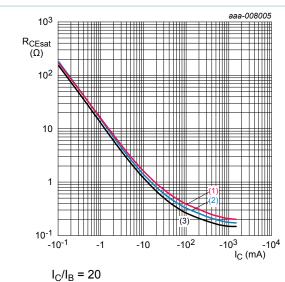


(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values



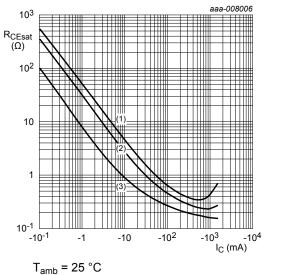
$$|c/|_{p} = 20$$

(1) 
$$T_{amb}$$
 = 100 °C

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 100$$

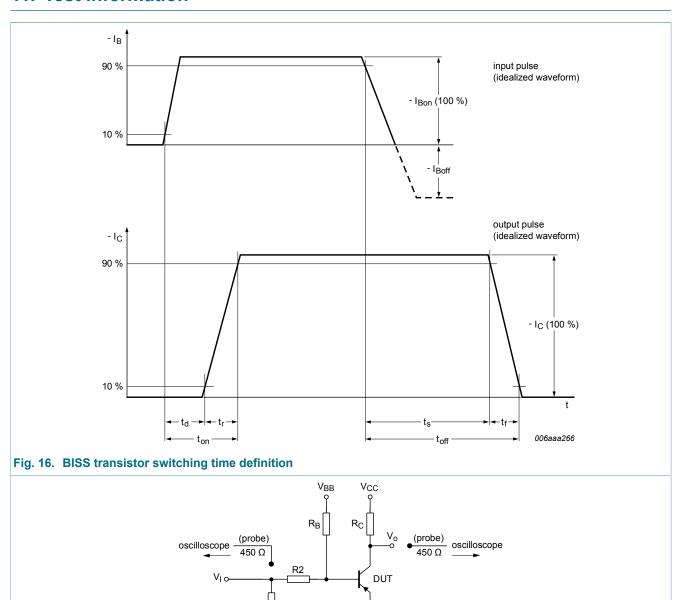
(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

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### 11. Test information



### 11.1 Quality information

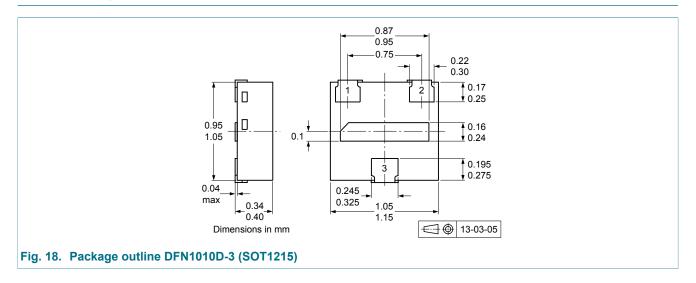
Fig. 17. Test circuit for switching times

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

mgd624

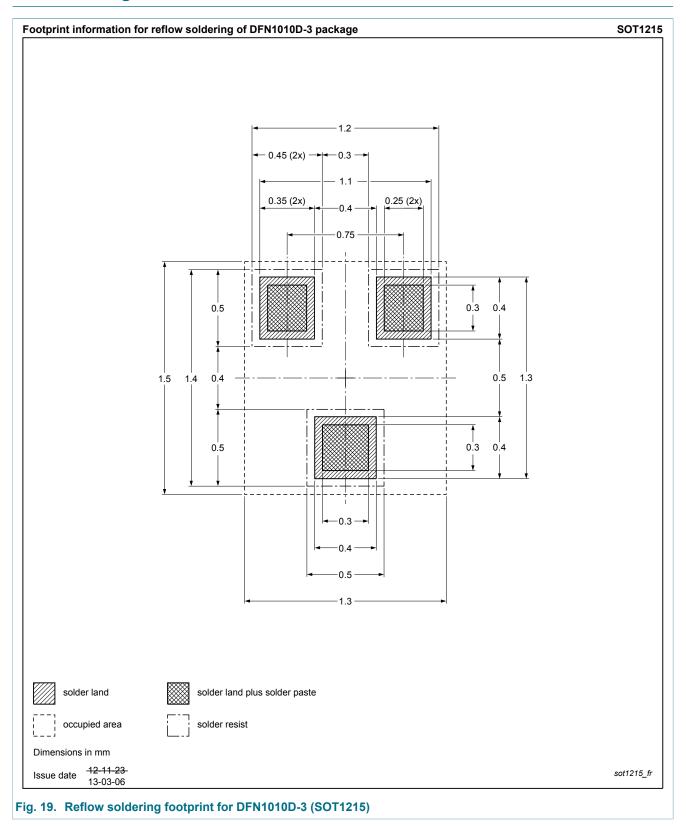
30 V, 1 A PNP low VCEsat (BISS) transistor

# 12. Package outline



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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5130QA v.1	20130828	Product data sheet	-	-

#### 30 V, 1 A PNP low VCEsat (BISS) transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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